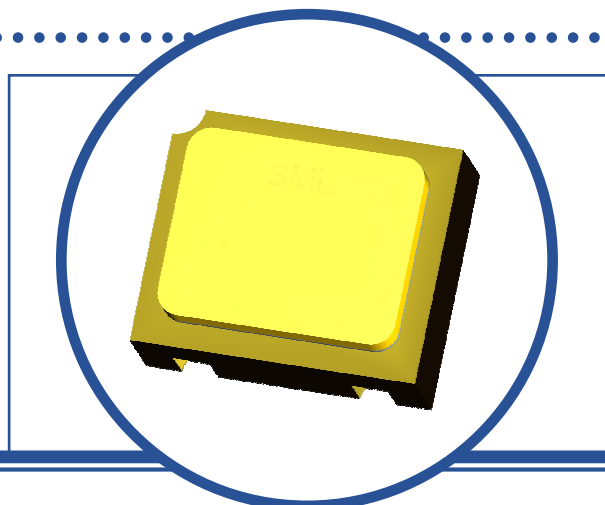


SCHOTTKY BARRIER DIODE

1N5711CSM

- High Breakdown Voltage ($V_{BR} = 70V$)
- Low Forward Voltage
- Hermetic Ceramic Surface Mount Package
- Suitable for Low Current, Fast Switching Applications.
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise stated)

V_{BR}	Breakdown Voltage	70V
V_{RRM}	Repetitive Peak Reverse Voltage	70V
I_F	Forward Current	15mA
P_D	Total Power Dissipation at $T_A = 25^\circ C$ Derate Above $25^\circ C$	250mW 2.5mW/ $^\circ C$
T_J	Junction Temperature Range	-55 to +125 $^\circ C$
T_{stg}	Storage Temperature Range	-65 to +150 $^\circ C$

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction To Ambient	400	$^\circ C/W$

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



SCHOTTKY BARRIER DIODE 1N5711CSM

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
V_{BR}	Breakdown Voltage	$I_R = 10\mu\text{A}$	70			V
$V_F^{(1)}$	Forward Voltage	$I_F = 1.0\text{mA}$			0.41	
		$I_F = 15\text{mA}$			1.0	
		$T_A = -55^\circ\text{C}$			1.1	
I_R	Reverse Current	$V_R = 50\text{V}$			200	nA
			$T_A = 125^\circ\text{C}$			200

DYNAMIC CHARACTERISTICS

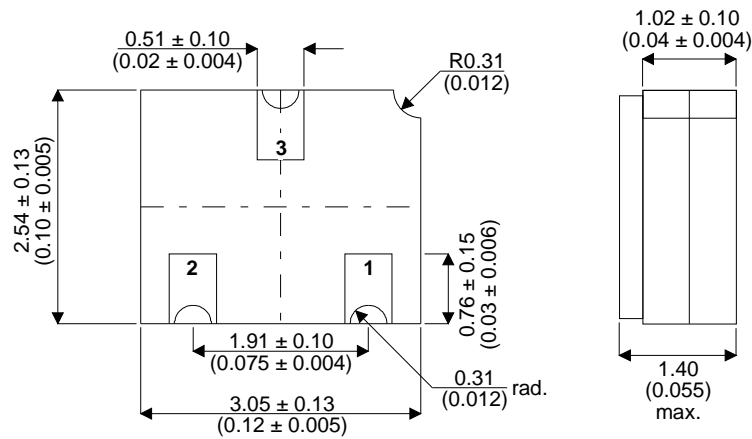
C_T	Capacitance	$V_R = 0\text{V}$	$f = 1.0\text{MHz}$		2.2	2.5	pF
$\tau^{(2)}$	Minority Carrier Lifetime	$I_F = 5\text{mA}$				100	ps

Notes

- (1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$
 (2) By design only, not a production test.

MECHANICAL DATA

Dimensions in mm (inches)



LCC1
(Underside View)

Pad 1 - Anode

Pad 2 - N/C

Pad 3 - Cathode